

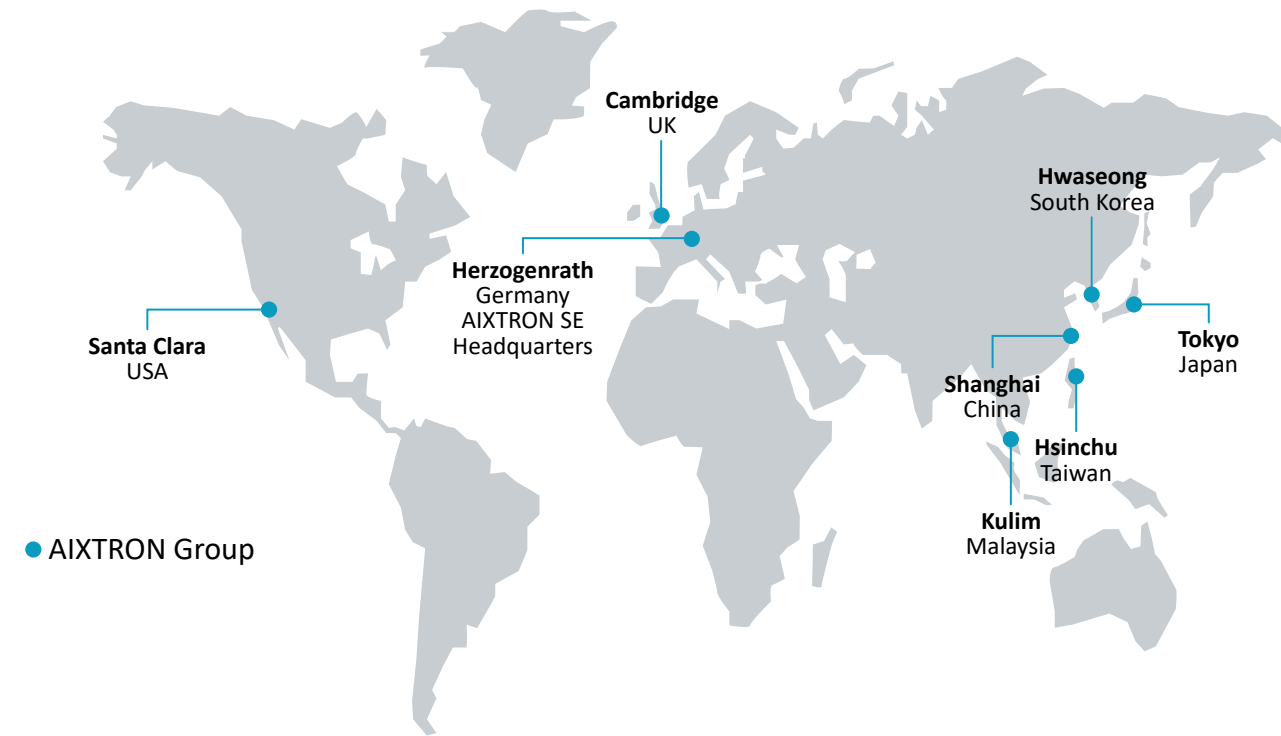


G10-GaN enables seamless process transfer from today's tool of record AIX G5+ C

- Same cassette-to-cassette wafer handling
- Identical process chamber size and wafer configuration
- „On-board“ calibration and control modes for process matching

AIXTRON

Global presence



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Deposition Systems for Compound Semiconductors

G10-GaN

150/200 mm high throughput epitaxy for GaN power & RF applications



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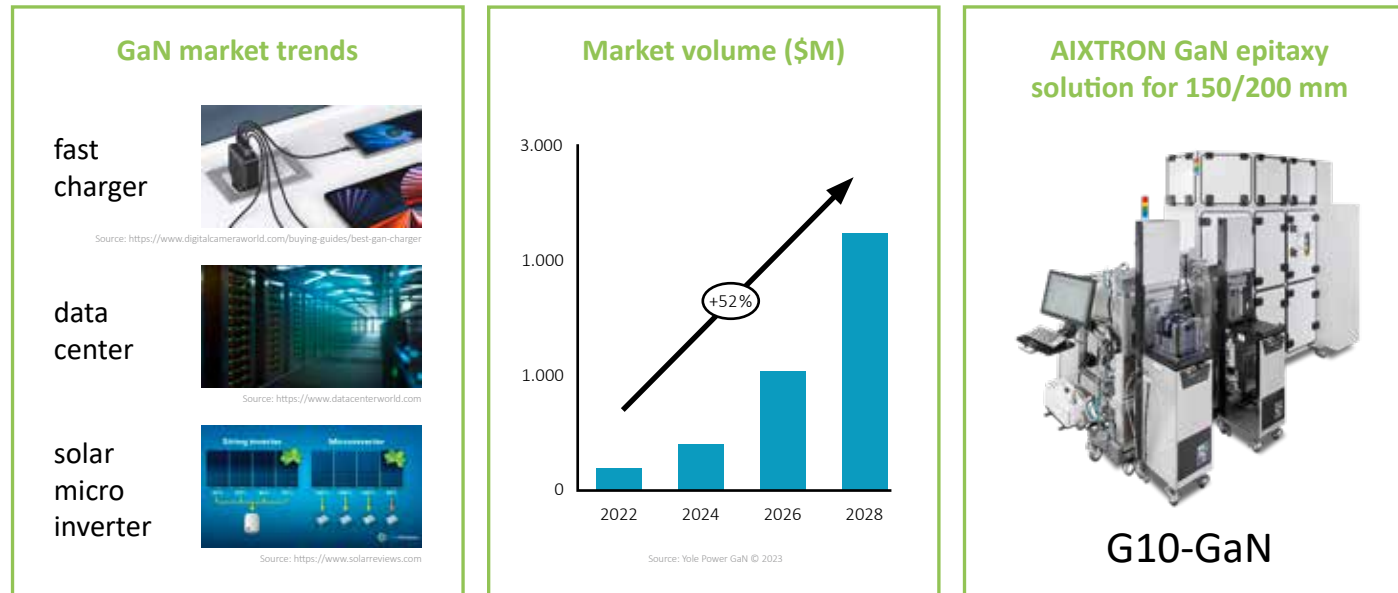
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High productivity MOCVD solution for 150/200 mm GaN power & RF applications

Market opportunity



G10-GaN

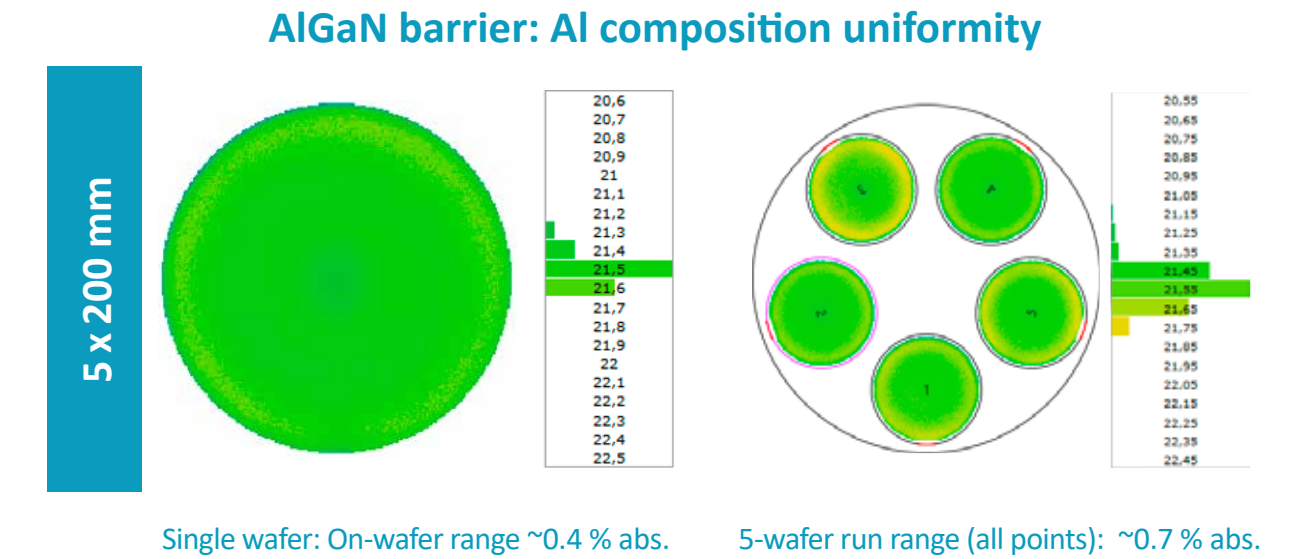
Planetary Reactor®



The best of both worlds

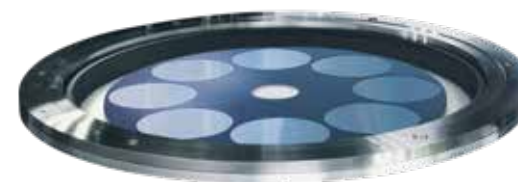
Single wafer performance at lowest batch processing cost

Composition uniformity



AIXTRON GaN

- **Highest wafer/m² fab area**
3 process chamber compact cluster design with 50 % footprint reduction
- **Best in class device yield**
3x on-wafer uniformity improvement at lowest particle level for all wafers (wafer-to-wafer, run-to-run, chamber-to-chamber)
- **Lowest epi cost/wafer in the market**
>25 % lower epi cost than any other platform



Your benefits

- **Highest wafer yield**
 - Low particle density (~0.1/cm²)
 - Excellent uniformity (on-wafer, wafer-to-wafer)
- **Best in class productivity**
 - Outstanding reproducibility
 - ≥90 % equipment uptime
- **Best in class epi cost**
 - Highest throughput/m² fab
 - Lowest labor & chemical cost

Our solutions

- Fully automated wafer handling (C2C)
- Novel wafer carrier design
- Individual wafer close loop topside temp. control
- Individual control of thickness & composition uniformity by 5-level gas injector
- Automated chamber cleaning
- Long lifetime consumables
- Smart system with predictive functionalities
- Advanced chamber-to-chamber matching capabilities
- Large capacity batch Planetary Reactor®
- Compact cluster design with 3 process chambers
- Highest chemical efficiency by 5-level gas injector
- Lowest operator assistance due to 50 wafer capacity with C2C

On-wafer device uniformity (650V application)

